

a second conductive capacitor plate; and

[a dielectric interposed between said first and second conductive capacitor plates, wherein said dielectric is an oxide of] a metal layer of a second material overlying the first conductive capacitor plate, wherein the metal layer includes a non-oxidized portion and an oxidized portion, wherein the oxidized portion is a dielectric of the capacitor; and

a processor configured to access the monolithic memory device.

53. (Amended) A capacitor comprising:

a first capacitor electrode;

[a dielectric layer that includes an oxide of] a metal layer overlying the first capacitor electrode, wherein the metal layer includes a non-oxidized portion and an oxidized portion, wherein the oxidized portion is a dielectric of the capacitor; and

a second capacitor electrode.

79. (Amended) The capacitor of claim 19, wherein the [oxide] oxidized portion of the metal layer is formed from at least one metal selected from the group consisting of titanium, copper, gold, tungsten, and nickel.

82. (Amended) The memory system of claim 20, wherein the [oxide] oxidized portion of the metal layer is formed from at least one metal selected from the group consisting of titanium, copper, gold, tungsten, and nickel.

85. (Amended) The capacitor of claim 53, wherein the [dielectric layer] oxidized portion of the metal layer is formed from at least one metal selected from the group consisting of titanium, copper, gold, tungsten, and nickel.

107. (Amended) The capacitor of claim 19, wherein the [oxide] oxidized portion of the metal layer comprises titanium.

108. (Amended) The capacitor of claim 19, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first conductive plate and the [oxide] oxidized portion of the metal layer.

109. (Amended) The memory system of claim 20, wherein the [oxide] oxidized portion of the metal layer comprises titanium.

110. (Amended) The memory system of claim 20, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first conductive plate and the [oxide] oxidized portion of the metal layer.

111. (Amended) The capacitor of claim 53, wherein the [dielectric layer] oxidized portion of the metal layer comprises titanium.

112. (Amended) The capacitor of claim 53, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first capacitor electrode and the [dielectric layer] oxidized portion of the metal layer.